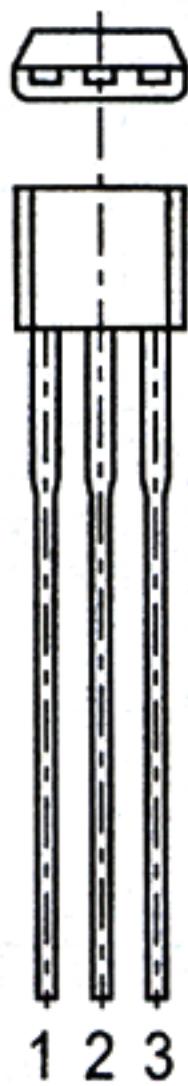


TO-92S Plastic-Encapsulate Transistors

2SC1740S TRANSISTOR(NPN)



TO-92S

- 1.BASE
- 2.COLLECTOR
- 3.EMITTER

FEATURES

Power dissipation

P_{CM} : 0.3 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 0.15 A

Collector-base voltage

$V_{(BR)CBO}$: 60 V

Operating and storage junction temperature range

T_J, T_{stg} : -55°C to + 150°C

ELECTRICAL CHARACTERISTICS

($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C= 50 \mu A, I_E=0$	60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C= 1 mA, I_B=0$	50		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E= 50 \mu A, I_C=0$	7		V
Collector cut-off current	I_{CBO}	$V_{CB}= 60 V, I_E=0$		0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}= 7 V, I_C=0$		0.1	μA
DC current gain	h_{FE}	$V_{CE}= 6 V, I_C= 1 mA$	120	560	
Collector-emitter saturation voltage	V_{CEsat}	$I_C= 50 mA, I_B= 5 mA$		0.4	V
Transition frequency	f_T	$V_{CE}= 12 V, I_C= 2 mA$ $f=100MHz$	100		MHz

CLASSIFICATION OF h_{FE}

Rank	Q	R	S
Range	120-270	180-390	270-560

Typical Characteristics

2SC1740S

